N-Channel 30-V (D-S) MOSFET

Key Features:

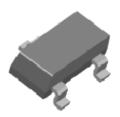
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

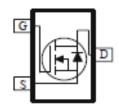
Typical	Ap	plica	atio	ns:
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- White LED boost converters
- · Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)	
30	160 @ V _{GS} = 10V	2.4	
30	250 @ V _{GS} = 4.5V	1.9	







ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage		V _{DS}	30	V		
Gate-Source Voltage			V_{GS}	±20	V	
Continuous Drain Current ^a		T _A =25°C	ı	2.4		
Continuous Drain Current		T _A =70°C	I _D	1.9	Α	
Pulsed Drain Current ^b			I _{DM}	10	L	
Continuous Source Current (Diode Conduction) a			I _S	1.9	Α	
Dower Dissinction a		T _A =25°C	P _D	1.3	W	
Power Dissipation ^a		T _A =70°C	ı D	0.8		
Operating Junction and Storage Temperature Range		T_J, T_{sta}	-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter			Maximum	Units		
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	100	°C/W		
Maximum Junction-to-Ambient	Steady State	IN _θ JΑ	166			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

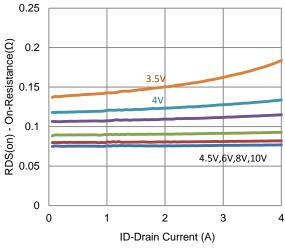
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	lana	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Brain Current	I _{DSS}	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	T UA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	5			Α	
Drain Cauras On Basistanas a	r	$V_{GS} = 10 \text{ V}, I_D = 1.9 \text{ A}$			160	mΩ	
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 1.6 \text{ A}$			250	11122	
Forward Transconductance a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 1.9 \text{ A}$		6		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = 0.95 \text{ A}, V_{GS} = 0 \text{ V}$		0.84		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$		1.4		nC	
Gate-Source Charge	Q_{gs}	$I_{DS} = 13 \text{ V}, \text{ V}_{GS} = 4.3 \text{ V},$ $I_{D} = 1.9 \text{ A}$		0.4			
Gate-Drain Charge	Q_gd	1B = 1.5 A		0.7			
Turn-On Delay Time	t _{d(on)}			2			
Rise Time	t _r	$V_{DS} = 15 \text{ V}, \text{ R}_{L} = 7.9 \Omega, \text{ I}_{D} = 1.9 \text{ A}, \\ V_{GEN} = 10 \text{ V}, \text{ R}_{GEN} = 6 \Omega$		5		ne	
Turn-Off Delay Time	$t_{d(off)}$			12		ns	
Fall Time	t _f			4			
Input Capacitance	C_{iss}			103			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		21		pF	
Reverse Transfer Capacitance	C_{rss}			16			

Notes

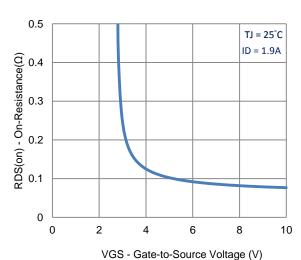
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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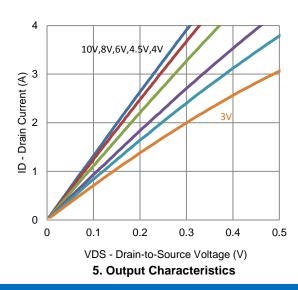
Typical Electrical Characteristics

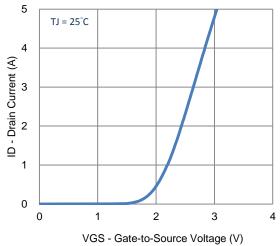


1. On-Resistance vs. Drain Current

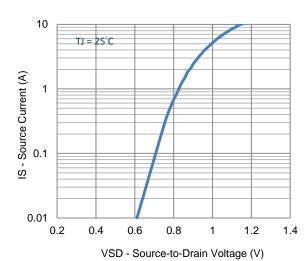


3. On-Resistance vs. Gate-to-Source Voltage

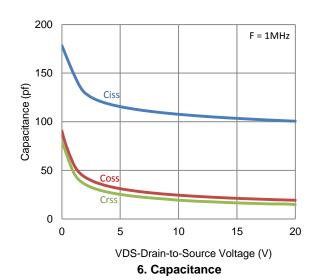




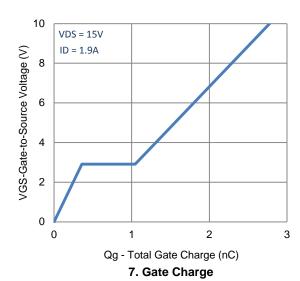
2. Transfer Characteristics

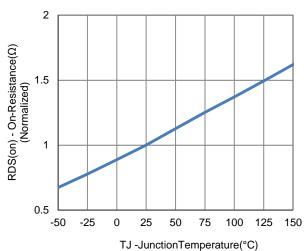


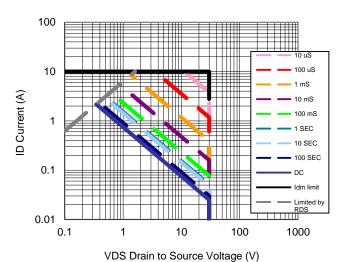
4. Drain-to-Source Forward Voltage



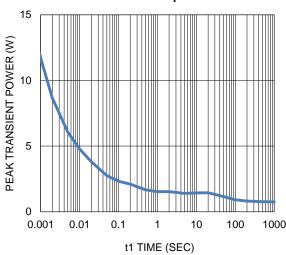
Typical Electrical Characteristics





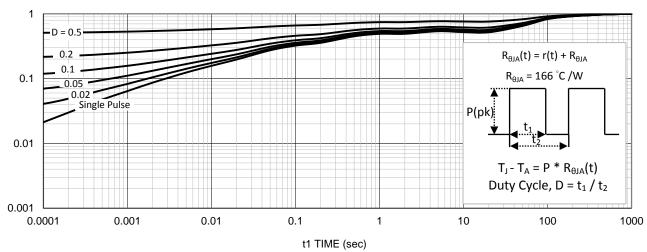


8. Normalized On-Resistance Vs Junction Temperature



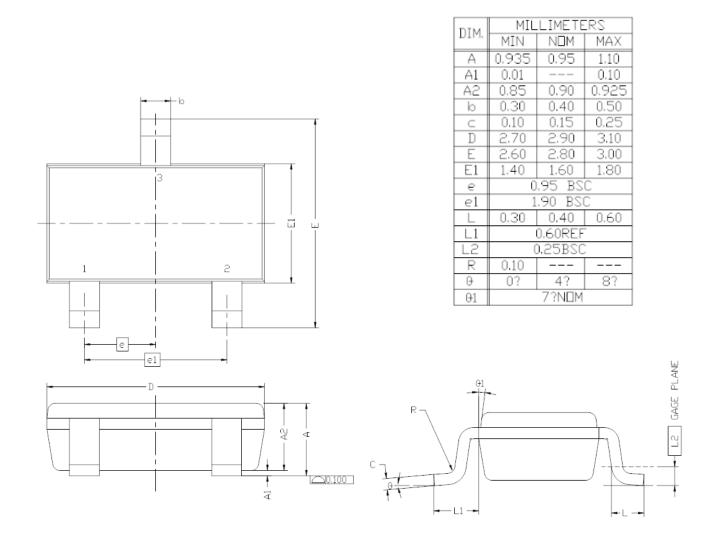
9. Safe Operating Area

10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



Note:

- 1. All Dimension Are In mm.
- Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
- 4. The Package Top May Be Smaller Than The Package Bottom.
- 5. Dimension "B" Does Not Include Dambar Protrusion. Allowable Dambar Protrusion Shall Be 0.08 mm Total In Excess Of "B" Dimension At Maximum Material Condition. The Dambar Cannot Be Located On The Lower Radius Of The Foot.